Quad 2-Channel Multiplexer with 3-State Outputs

The MC74VHCT257A is an advanced high speed CMOS quad 2-channel multiplexer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

It consists of four 2-input digital multiplexers with common select (S) and enable (\overline{OE}) inputs. When (\overline{OE}) is held High, selection of data is inhibited and all the outputs go Low.

The select decoding determines whether the A or B inputs get routed to the corresponding Y outputs.

The VHCT inputs are compatible with TTL levels. This device can be used as a level converter for interfacing 3.3 V to 5.0 V because it has full 5 V CMOS level output swings.

The VHCT257A input structures provide protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. The output structures also provide protection when $V_{CC}=0$ V. These input and output structures help prevent device destruction caused by supply voltage—input/output voltage mismatch, battery backup, hot insertion, etc.

The internal circuit is composed of three stages, including a buffered output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

- High Speed: $t_{PD} = 4.1 \text{ ns (Typ)}$ at $V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation: $I_{CC} = 4.0 \mu A$ (Max) at $T_A = 25$ °C
- TTL-Compatible Inputs: $V_{IL} = 0.8 \text{ V}$; $V_{IH} = 2.0 \text{ V}$
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Designed for 2.0 V to 5.5 V Operating Range
- Low Noise: $V_{OLP} = 0.8 \text{ V (Max)}$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; Machine Model > 200 V

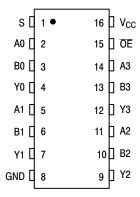


Figure 1. Pin Assignment



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MARKING DIAGRAMS

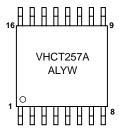


SO-16 D SUFFIX CASE 751B





TSSOP-16 DT SUFFIX CASE 948F





EIAJ SO-16 M SUFFIX CASE 966



A = Assembly Location

L, WL = Wafer Lot Y = Year W, WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74VHCT257AD	SO-16	48 Units/Rail
MC74VHCT257ADR2	SO-16	2500 Tape & Reel
MC74VHCT257ADT	TSSOP-16	96 Units/Rail
MC74VHCT257ADTR2	TSSOP-16	2500 Tape & Reel
MC74VHCT257AM	EIAJSO-16	50 Units/Rail
MC74VHCT257AMEL	EIAJSO-16	2000 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

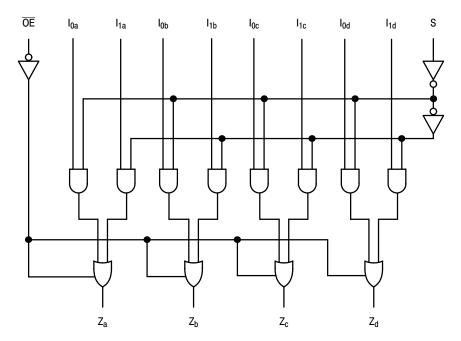


Figure 2. Expanded Logic Diagram

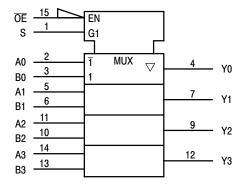


Figure 3. IEC Logic Symbol

FUNCTION TABLE

Inp	Inputs			
OE	S	Outputs Y0 – Y3		
Н	Х	Z		
L	L	A0-A3		
L	Н	B0-B3		

A0 - A3, B0 - B3 = the levels of the respective Data–Word Inputs.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or $V_{\rm CC}$). Unused outputs must be left open.

MAXIMUM RATINGS

Symbol	Pa	rameter	Value	Unit
V _{CC}	Positive DC Supply Voltage		-0.5 to +7.0	V
V _{IN}	Digital Input Voltage		-0.5 to +7.0	V
V _{OUT}	DC Output Voltage	Output in 3-State High or Low State	-0.5 to +7.0 -0.5 to V _{CC} +0.5	V
I _{IK}	Input Diode Current		-20	mA
l _{OK}	Output Diode Current		±20	mA
I _{OUT}	DC Output Current, per Pin		±25	mA
Icc	DC Supply Current, V _{CC} and GND Pins		±75	mA
P _D	Power Dissipation in Still Air	SOIC Package TSSOP	200 180	mW
T _{STG}	Storage Temperature Range		-65 to +150	°C
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 1) Machine Model (Note 2) Charged Device Model (Note 3)	>2000 >200 >2000	V
I _{LATCHUP}	Latchup Performance	Above V _{CC} and Below GND at 125°C (Note 4)	±300	mA
$\theta_{\sf JA}$	Thermal Resistance, Junction-to-Ambie	ent SOIC Package TSSOP	143 164	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

- 1 Tested to EIA/JESD22-A114-A
- 2 Tested to EIA/JESD22-A115-A
- 3 Tested to JESD22-C101-A
- 4 Tested to EIA/JESD78

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit	
V _{CC}	DC Supply Voltage		4.5	5.5	V
V _{IN}	DC Input Voltage		0	5.5	V
V _{OUT}	DC Output Voltage		0	5.5	V
T _A	Operating Temperature Range, all Package Types		-55	125	°C
t _r , t _f	Input Rise or Fall Time V _{CC}	= 5.0 V <u>+</u> 0.5 V	0	20	ns/V

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

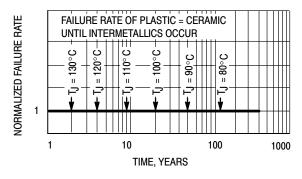


Figure 4. Failure Rate vs. Time Junction Temperature

DC CHARACTERISTICS (Voltages Referenced to GND)

			V _{CC}	1	Γ _A = 25°	С	T _A ≤	85°C	-55°C ≤ 1	T _A ≤ 125°C	
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		4.5 to 5.5	2			2		2		V
V _{IL}	Maximum Low-Level Input Voltage		4.5 to 5.5			0.8		0.8		0.8	V
V _{OH}	Maximum High-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu A$	4.5	3.94			3.8		3.66		V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -8 \text{ mA}$	4.5	3.94			3.8		3.66		
V _{OL}	Maximum Low-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu A$	4.5		0	0.1		0.1		0.1	V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = 8 \text{ mA}$	4.5			0.36		0.44		0.52	
I _{IN}	Input Leakage Current	$V_{IN} = 5.5 \text{ V or GND}$	0 to 5.5			±0.1		±1.0		±1.0	μΑ
l _{OZ}	Maximum 3–State Leakage Current	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$	5.5			±0.25		±2.5		±2.5	μΑ
Ісст	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			1.35		1.5		1.65	mA
Icc	Additional Quiescent Supply Current (per pin)	$V_{IN} = V_{CC}$ or GND	5.5			4.0		40		40	μΑ
I _{OPD}	Output Leakage Current	V _{OUT} = 5.5 V	0			0.5		5		5	μΑ

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ns}$)

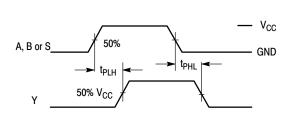
				T _A = 25°C		$T_A = 25^{\circ}C$ $T_A = \leq 85^{\circ}C$		-55°C ≤ T	' _A ≤ 125°C		
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay,	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15 pF$ $C_L = 50 pF$		5.8 8.3	9.3 12.8	1.0 1.0	11.0 14.5	1.0 1.0	11.0 14.5	ns
	A or B to Y	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	$C_L = 15 pF$ $C_L = 50 pF$		3.6 5.1	5.9 7.9	1.0 1.0	7.0 9.0	1.0 1.0	7.0 9.0	
t _{PLH} , t _{PHL}	Maximum Propagation Delay,	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15 pF$ $C_L = 50 pF$		7.0 9.5	11.0 14.5	1.0 1.0	13.0 16.5	1.0 1.0	13.0 16.5	ns
S to Y	S to Y	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	$C_L = 15 pF$ $C_L = 50 pF$		4.0 5.5	6.8 8.8	1.0 1.0	8.0 10.0	1.0 1.0	8.0 10.0	
t _{PZL} , t _{PZH}	Maximum Output Enable,	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $R_L = 1 \text{ k}\Omega$	$C_L = 15 pF$ $C_L = 50 pF$		6.7 9.2	10.5 14.0	1.0 1.0	12.5 16.0	1.0 1.0	12.5 16.0	ns
	Time, OE to Y	$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $R_L = 1 \text{ k}\Omega$	$C_L = 15 pF$ $C_L = 50 pF$		3.6 5.1	6.8 11.0	1.0 12.0	8.0 10.0	1.0 1.0	8.0 12.0	
t _{PLZ} , t _{PHZ}		$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $R_L = 1 \text{ k}\Omega$	C _L = 50 pF		10.5	14.0	1.0	15.0	1.0	15.0	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $R_L = 1 \text{ k}\Omega$	C _L = 50 pF		9.5	12.0	1.0	13.0	1.0	13.0	
C _{IN}	Maximum Input Capacitance				4	10		10		10	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Note 5)	20	pF

^{5.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC} \cdot C_{PD}$ is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

NOISE CHARACTERISTICS (Input $t_{r} = t_{f} = 3.0$ ns, $C_{L} = 50$ pF, $V_{CC} = 5.0$ V)

		T _A = 25°C		
Symbol	Characteristic	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.3	0.8	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	- 0.3	- 0.8	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V



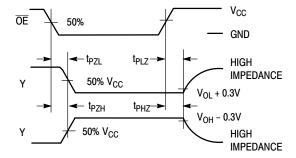
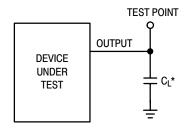
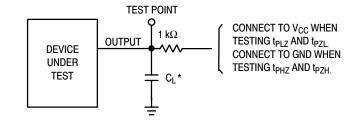


Figure 5. Switching Waveform

Figure 6. Switching Waveform



*Includes all probe and jig capacitance



*Includes all probe and jig capacitance

Figure 7. Test Circuit

Figure 8. Test Circuit

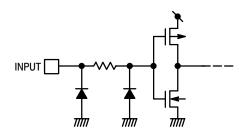
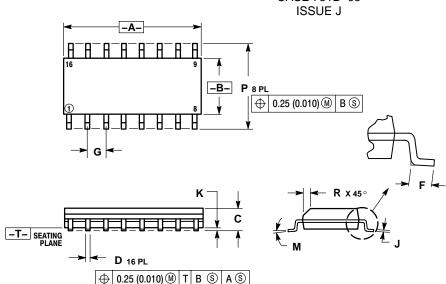


Figure 9. Input Equivalent Circuit

PACKAGE DIMENSIONS





NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
 Y14.5M. 1982.

- Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

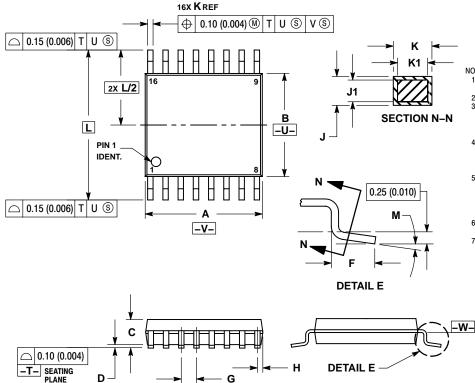
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMILIM MATERIAL CONDITION. MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	HES		
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
C	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
_	0.19	0.25	0.008	0.009	
Κ	0.10	0.25	0.004	0.009	
M	0°	7°	0 °	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

TSSOP-16 **DT SUFFIX** CASE 948F-01 **ISSUE O**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- DIMENSIONING AND TOLERANGING FET AND Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- (0.006) PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

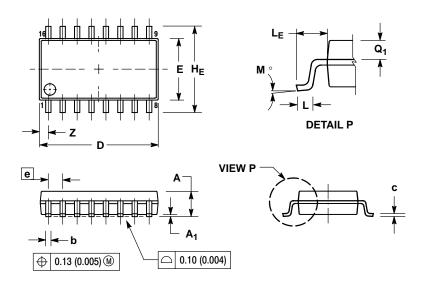
 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. SHALL BE 0.08 (0.003) TOTAL IN EXCECT OF THE NUMBER SHALL BE 1.08 (0.003) TOTAL IN EXCECT STUE NUMBERSION.
- EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
C		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.18	0.28	0.007	0.011	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40		0.252 BSC		
M	0°	8°	0°	8°	

PACKAGE DIMENSIONS

SOIC EIAJ-16 M SUFFIX CASE 966-01 **ISSUE O**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS I			HES			
DIM	MIN	MAX	MIN	MAX			
Α		2.05		0.081			
A ₁	0.05	0.20	0.002	0.008			
b	0.35	0.50	0.014	0.020			
С	0.18	0.27	0.007	0.011			
D	9.90	10.50	0.390	0.413			
Е	5.10	5.45	0.201	0.215			
е	1.27	BSC	0.050	BSC			
HE	7.40	8.20	0.291	0.323			
L	0.50	0.85	0.020	0.033			
LE	1.10	1.50	0.043	0.059			
M	0 °	10 °	0 °	10°			
Q ₁	0.70	0.90	0.028	0.035			
Z		0.78		0.031			

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